



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

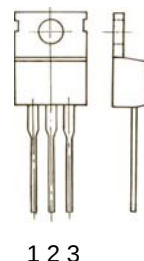
2SC4544 TRANSISTOR (NPN)

FEATURES

- High voltage: $V_{(BR)CEO} = 300\text{ V}$
- Small collector output capacitance: $C_{ob}=3.0\text{pF}$ (typ.)
- Collector metal (fin) is fully covered with mold resin.

TO-220

1. BASE
2. COLLECTOR
3. EMITTER



MAXIMUM RATINGS* $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Dissipation	2	W
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{ mA}, I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=240\text{V}, I_E=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			1.0	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C=4\text{mA}$	20			
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=20\text{mA}$	30		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			1.0	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=20\text{mA}$	50	70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1\text{MHz}$		3.0		pF

Typical Characteristics

2SC4544

